Power MOSFETS

DATASHEET

LM45180NAI8A

N-Channel

Enhancement Mode MOSFET

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Quality Management Systems

ISO 9001:2015 Certificate

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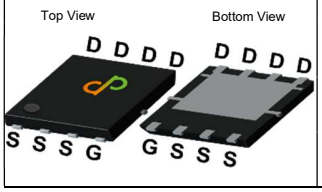
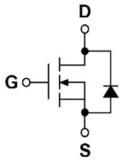
N-Channel Enhancement Mode MOSFET

Pin Description

PDFN3.3*3.3



Symbol



Product Summary

Symbol	N-Channel	Unit
V_{DSS}	45	V
$R_{DS(ON)\text{-}Max}$	18	mΩ
ID	30	A

Feature

- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS Tested

Applications

- Power Management in Notebook Computer
- Portable Equipment and Battery Powered systems

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM45180NAI8A	PDFN3.3*3.3	Tape & Reel	5000 / Tape & Reel	45180 □□□□□□

Note：□□□□□□ = Lot Code

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		45	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C=25°C	27	A
I_{DM}①	Pulse Drain Current Tested	T_C=25°C	71	A
I_D	Continuous Drain Current	T_C=25°C	30	A
		T_C=100°C	19	
P_D	Maximum Power Dissipation	T_C=25°C	30	W
		T_C=100°C	12	
I_D	Continuous Drain Current	T_A=25°C	6.2	A
		T_A=70°C	5	
P_D	Maximum Power Dissipation	T_A=25°C	1.3	W
		T_A=70°C	0.8	
I_{AS}②	Avalanche Current, Single pulse	L=0.1mH	18	A
E_{AS}②	Avalanche Energy, Single pulse	L=0.1mH	16	mJ

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	4.2	°C/W
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	Steady State	95	°C/W

Note ①：Max. current is limited by bonding wire

Note ②：UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③：Surface Mounted on 1in^2 FR-4 board with 1oz

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	45	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=36 V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	1.2	1.7	2	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$④	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A	-	15	18	mΩ
		V_{GS}=4.5V, I_{DS}=15A	-	16.8	22	
gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=5A	-	11	-	S
Dynamic Characteristics ⑤						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, Freq.=1MHz	-	3.4	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, Freq.=1MHz	-	1048	-	pF
C_{oss}	Output Capacitance		-	83	-	
C_{rss}	Reverse Transfer Capacitance		-	64	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=20V, I_D=1A,R_{GEN}=6Ω	-	5.7	-	nS
t_r	Turn-on Rise Time		-	21.2	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	39.8	-	
t_f	Turn-off Fall Time		-	19.2	-	
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=25V I_D=14A	-	12.6	-	nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=25V, I_D=14A	-	25.1	-	
Q_{gs}	Gate-Source Charge		-	1.5	-	
Q_{gd}	Gate-Drain Charge		-	6.8	-	
Source-Drain Characteristics						
V_{SD}④	Diode Forward Voltage	I_{SD}=1A, V_{GS}=0V	-	0.75	1.1	V
t_{rr}	Reverse Recovery Time	I_F=1A, V_R=0V dI_F/dt=100A/μs	-	12.8	-	nS
Q_{rr}	Reverse Recovery Charge		-	6.2	-	nC

Note ④：Pulse test (pulse width≤300us, duty cycle≤2%).
Note ⑤：Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

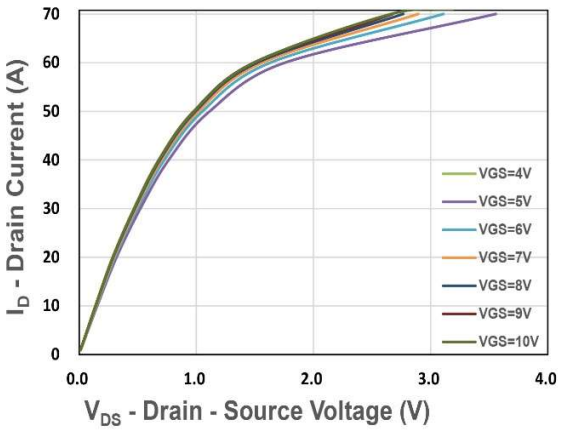


Figure 1. Output Characteristics

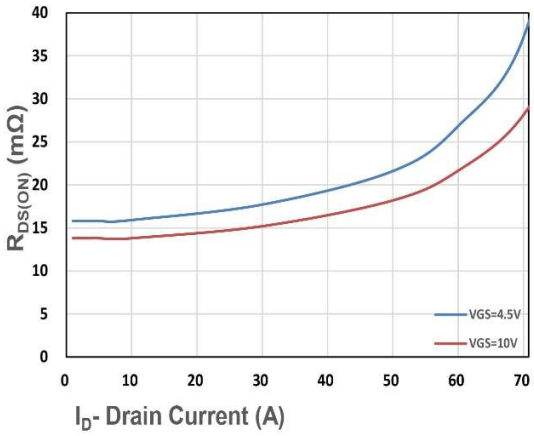


Figure 2. On-Resistance vs. ID

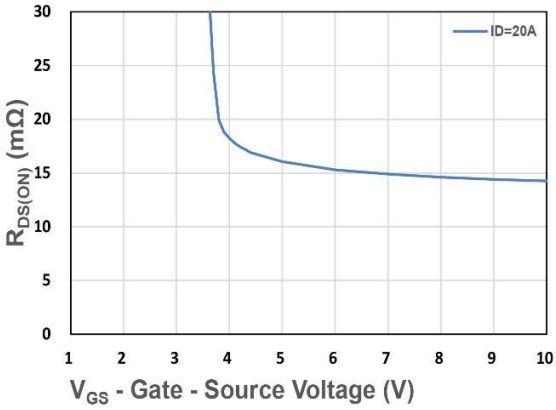


Figure 3. On-Resistance vs. VGS

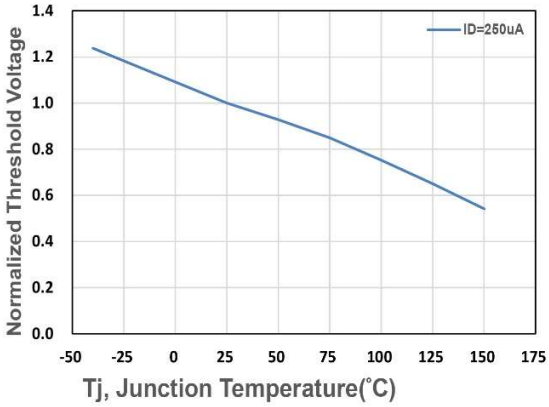


Figure 4. Gate Threshold Voltage

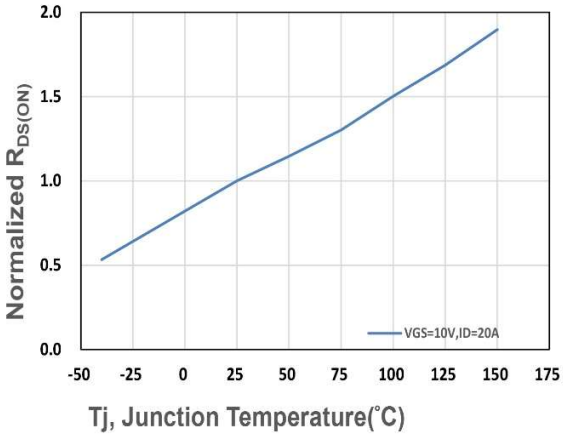


Figure 5. Drain-Source On Resistance

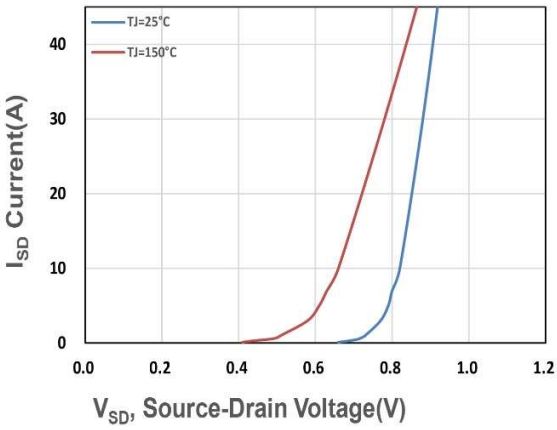


Figure 6. Source-Drain Diode Forward

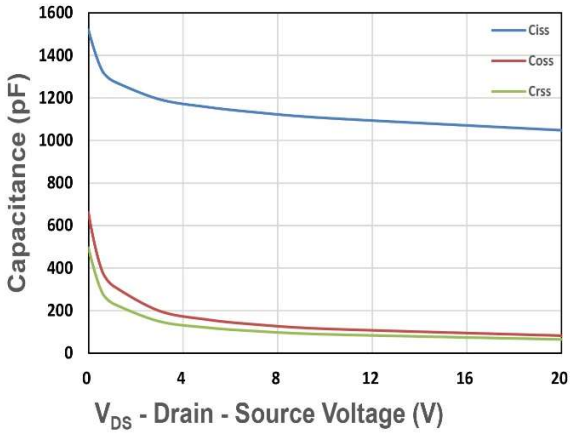


Figure 7. Capacitance

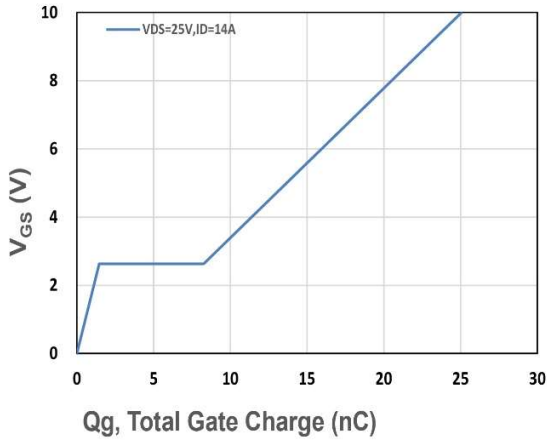


Figure 8. Gate Charge Characteristics

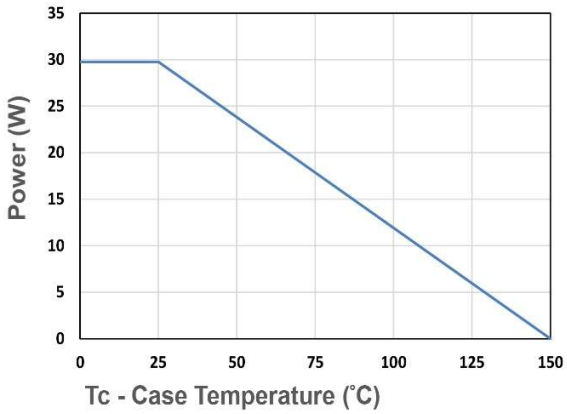


Figure 9. Power Dissipation

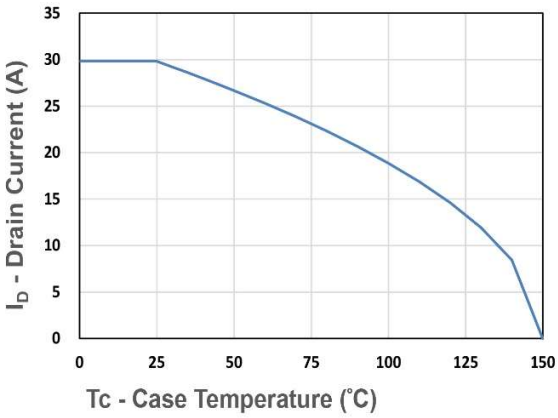


Figure 10. Drain Current

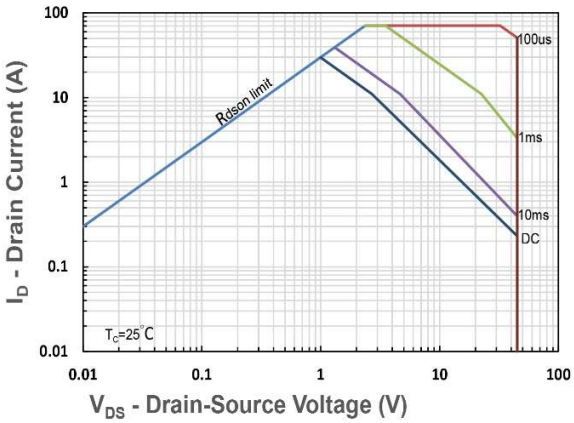


Figure 11. Safe Operating Area

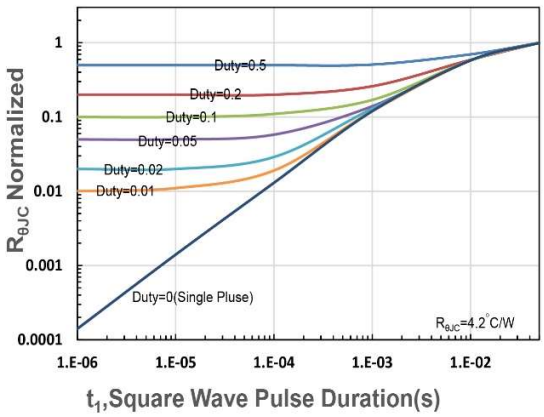


Figure 12. RθJC Transient Thermal Impedance